



YOUSHANG SEMICONDUCTOR

**设计研发新型功率器件**

**各类小信号开关**

**中低压及高压大电流等场效应管**

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企业微信二维码



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## Features

- $BV_{CEO} > 100V$
- $I_C = 6A$  High Continuous Collector Current
- $I_{CM} = 10A$  Peak Pulse Current
- Low Saturation Voltage  $V_{CE(sat)} < 35mV$
- $R_{SAT} = 36m\Omega$  at 6A for a Low Equivalent On-Resistance
- $h_{FE}$  Specified Up to 10A for a High Gain Hold Up
- Complementary PNP Type: NK-ZX5T953G

## Mechanical Data

- Case: SOT223
- Case Material: Molded Plastic. "Green" Molding Compound; UL Flammability Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish - Matte Tin Plated Leads; Solderable per MIL-STD-202, Method 208 ③
- Weight: 0.112 grams (Approximate)

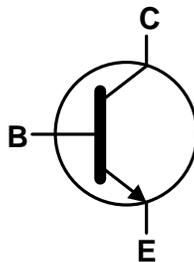
## Applications

- Motor Driving
- Line Switching
- High Side Switches

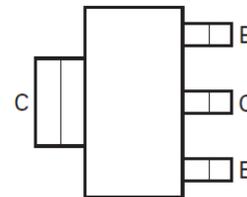
SOT223



Top View



Device Symbol



Top View  
Pin-Out

### Absolute Maximum Ratings (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V <sub>CBO</sub>	200	V
Collector-Emitter Voltage	V <sub>CEO</sub>	100	V
Emitter-Base Voltage	V <sub>EBO</sub>	7	V
Continuous Collector Current	I <sub>C</sub>	6	A
Peak Pulse Current	I <sub>CM</sub>	10	A

### Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

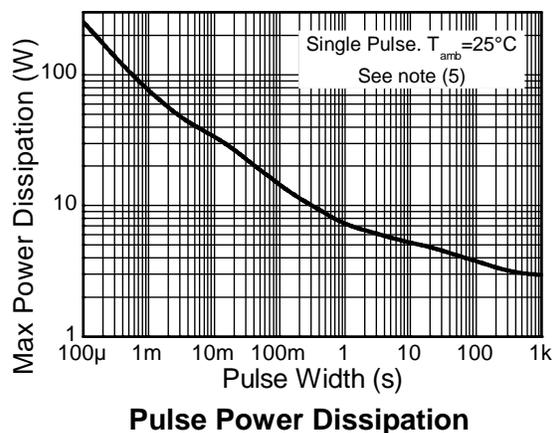
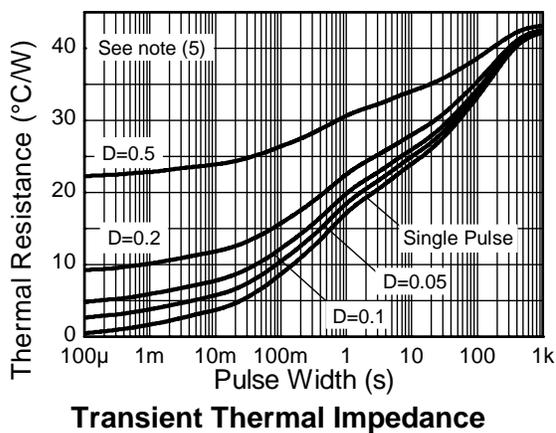
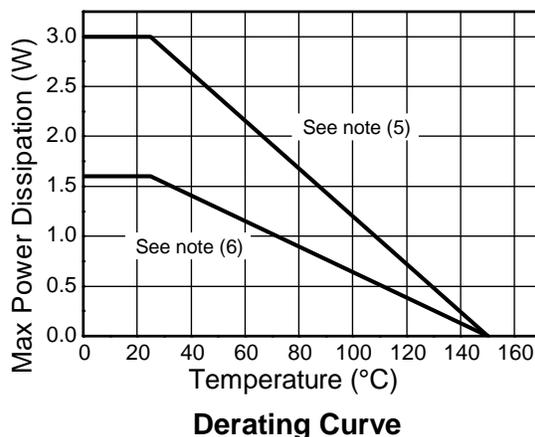
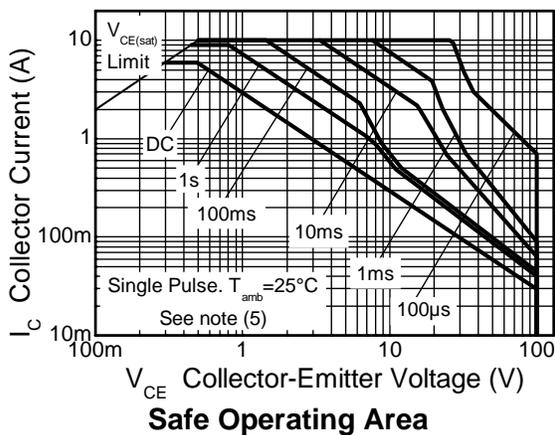
Characteristic	Symbol	Value	Unit
Power Dissipation Linear Derating Factor	P <sub>D</sub>	3.0	W
		24	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	1.6	mW/°C
		12.8	
Thermal Resistance, Junction to Ambient	R <sub>θJA</sub>	42	°C/W
		78	
Thermal Resistance Junction to Lead	R <sub>θJL</sub>	10.5	
Operating and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

### ESD Ratings (Note 8)

Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	C

- Notes:
- For a device surface mounted on 52mm x 52mm x 1.6mm FR4 PCB with high coverage of single sided 2oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
  - Same as Note 5, except the device is surface mounted on 25mm x 25mm with 1oz copper.
  - Thermal resistance from junction to solder-point (at the end of the collector lead).
  - Refer to JEDEC specification JESD22-A114 and JESD22-A115.

## Thermal Characteristics and Derating Information

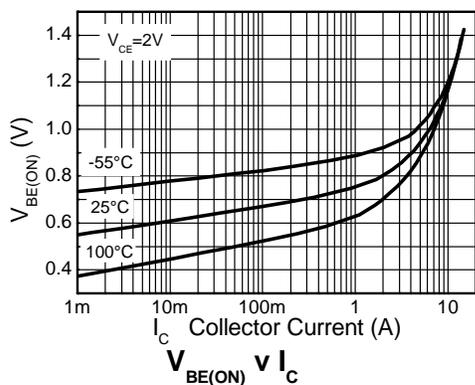
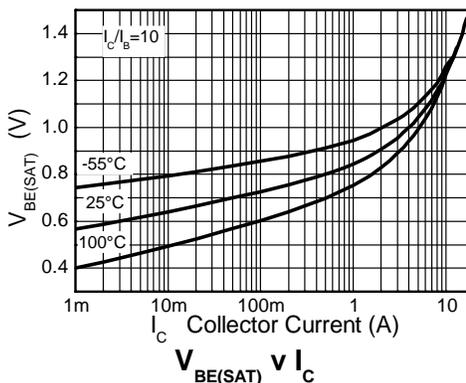
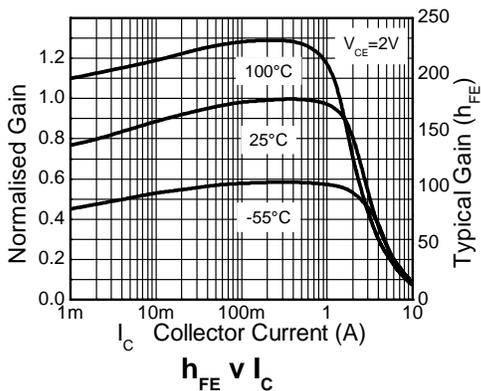
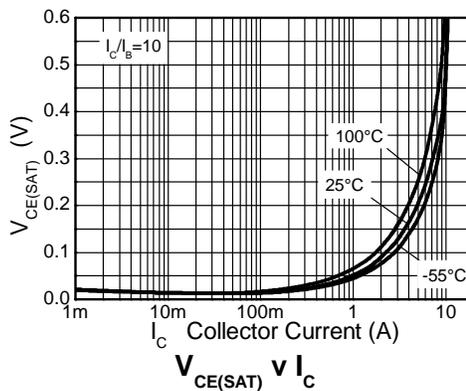
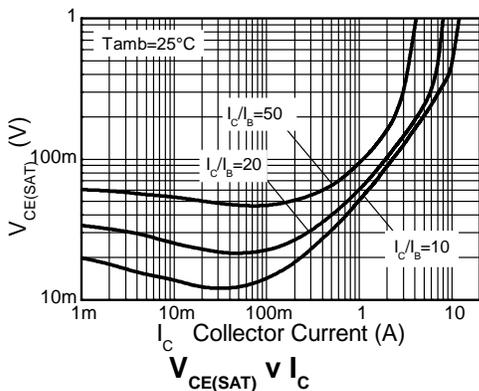


**Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

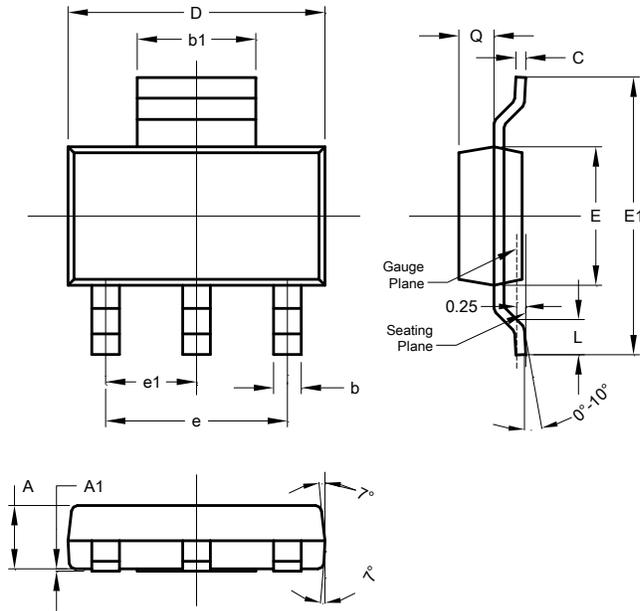
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV <sub>CBO</sub>	200	235	-	V	I <sub>C</sub> = 100μA
Collector-Emitter Breakdown Voltage	BV <sub>CER</sub>	200	235	-	V	I <sub>C</sub> = 1μA, R <sub>B</sub> ≤ 1kΩ
Collector-Emitter Breakdown Voltage (Note 9)	BV <sub>CEO</sub>	100	115	-	V	I <sub>C</sub> = 10mA
Emitter-Base Breakdown Voltage	BV <sub>EBO</sub>	7	8.1	-	V	I <sub>E</sub> = 100μA
Collector-Base Cut-Off Current	I <sub>CBO</sub>	-	<1	20	nA	V <sub>CB</sub> = 150V
				0.5	μA	V <sub>CB</sub> = 150V, T <sub>A</sub> = +100°C
Collector-Emitter Cut-Off Current	I <sub>CER</sub>	-	-	20	nA	V <sub>CB</sub> = 150V
	R ≤ 1kΩ			0.5	μA	V <sub>CB</sub> = 150V, T <sub>A</sub> = +100°C
Emitter Cut-Off Current	I <sub>EBO</sub>	-	-	10	nA	V <sub>EB</sub> = 6V
Static Forward Current Transfer Ratio (Note 9)	h <sub>FE</sub>	100	230	-	-	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 2V
		100	200	300		I <sub>C</sub> = 2A, V <sub>CE</sub> = 2V
		30	60	-		I <sub>C</sub> = 5A, V <sub>CE</sub> = 2V
		10	20	-		I <sub>C</sub> = 10A, V <sub>CE</sub> = 2V
Collector-Emitter Saturation Voltage (Note 9)	V <sub>CE(sat)</sub>	-	21	35	mV	I <sub>C</sub> = 100mA, I <sub>B</sub> = 5mA
		-	50	65		I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA
		-	95	125		I <sub>C</sub> = 2A, I <sub>B</sub> = 100mA
		-	180	220		I <sub>C</sub> = 5A, I <sub>B</sub> = 500mA
Base-Emitter Saturation Voltage (Note 9)	V <sub>BE(sat)</sub>	-	1,020	1,120	mV	I <sub>C</sub> = 5A, I <sub>B</sub> = 500mA
Base-Emitter Turn-On Voltage (Note 9)	V <sub>BE(on)</sub>	-	920	1,000	mV	I <sub>C</sub> = 5A, V <sub>CE</sub> = 2V
Output Capacitance (Note 9)	C <sub>obo</sub>	-	26	-	pF	V <sub>CB</sub> = 10V, f = 1MHz
Transition Frequency	f <sub>T</sub>	-	130	-	MHz	V <sub>CE</sub> = 10V, I <sub>C</sub> = 100mA f = 50MHz
Switching Time	t <sub>on</sub>	-	41	-	ns	V <sub>CC</sub> = 10V, I <sub>C</sub> = 1A I <sub>B1</sub> = -I <sub>B2</sub> = 100mA
	t <sub>off</sub>	-	1,010	-		

Note: 9. Measured under pulsed conditions. Pulse width ≤ 300μs. Duty cycle ≤ 2%.

**Typical Electrical Characteristics** (@ $T_A = +25^\circ\text{C}$ , unless otherwise specified.)

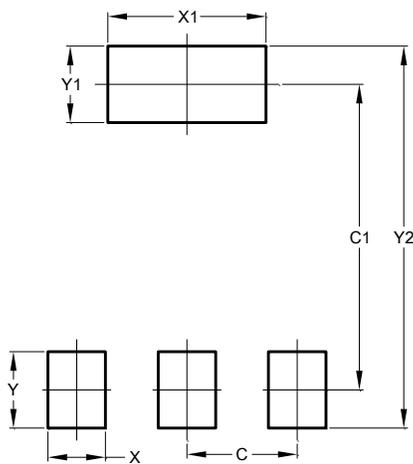


### Package Outline Dimensions



SOT223			
Dim	Min	Max	Typ
A	1.55	1.65	1.60
A1	0.010	0.15	0.05
b	0.60	0.80	0.70
b1	2.90	3.10	3.00
C	0.20	0.30	0.25
D	6.45	6.55	6.50
E	3.45	3.55	3.50
E1	6.90	7.10	7.00
e	-	-	4.60
e1	-	-	2.30
L	0.85	1.05	0.95
Q	0.84	0.94	0.89
All Dimensions in mm			

### Suggested Pad Layout



Dimensions	Value (in mm)
C	2.30
C1	6.40
X	1.20
X1	3.30
Y	1.60
Y1	1.60
Y2	8.00